

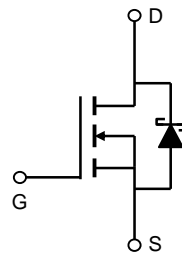
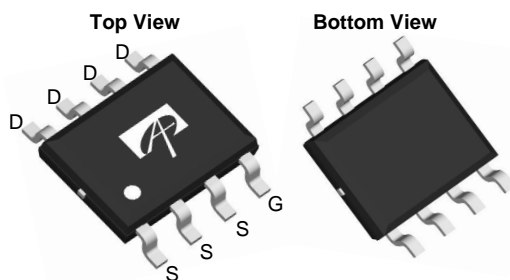
General Description

SRFET™ The AO4718 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$, and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

Features

V_{DS} (V) = 30V
 $I_D = 15A$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 9m\Omega$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 14m\Omega$ ($V_{GS} = 4.5V$)

100% UIS Tested
 100% Rg Tested


SOIC-8

SRFET™
 Soft Recovery MOSFET:
 Integrated Schottky Diode

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^{AF}	I_{DSM}	$T_A=25^\circ\text{C}$	15
		$T_A=70^\circ\text{C}$	12
Pulsed Drain Current ^B	I_{DM}	80	A
Avalanche Current ^B	I_{AS}, I_{AR}	25	
Avalanche energy $L=0.3\text{mH}$ ^B	E_{AS}, E_{AR}	94	mJ
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2.0
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10\text{s}$	32	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	60	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	17	24	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			0.1 10	mA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			0.1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.3	1.65	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	80			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=15\text{A}$ $T_J=125^\circ\text{C}$		7.3 10.3	9 13	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=12\text{A}$		10.8	14	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=15\text{A}$		43		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.41	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		1620	1950	pF
C_{oss}	Output Capacitance			382		pF
C_{rss}	Reverse Transfer Capacitance			162		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.2	1.8	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=15\text{A}$		24.7	32	nC
$Q_g(4.5\text{V})$	Total Gate Charge			12	16	nC
Q_{gs}	Gate Source Charge			4.0		nC
Q_{gd}	Gate Drain Charge			5.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1\Omega$, $R_{GEN}=3\Omega$		6.3		ns
t_r	Turn-On Rise Time			9.3		ns
$t_{D(off)}$	Turn-Off DelayTime			21.6		ns
t_f	Turn-Off Fall Time			5.4		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=15\text{A}$, $di/dt=300\text{A}/\mu\text{s}$		19	23	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=15\text{A}$, $di/dt=300\text{A}/\mu\text{s}$		36.4		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ junction to ambient thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

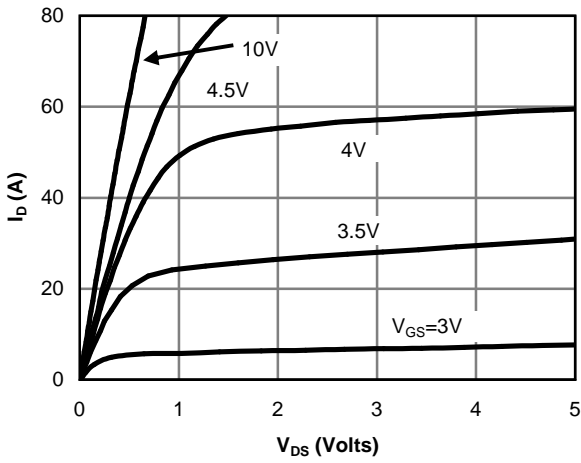


Figure 1: On-Region Characteristics

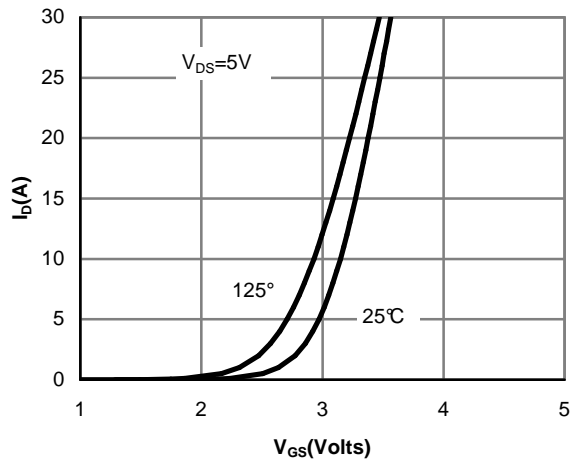


Figure 2: Transfer Characteristics

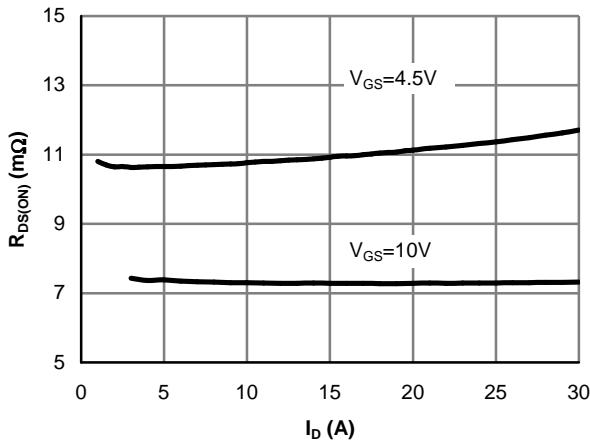


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

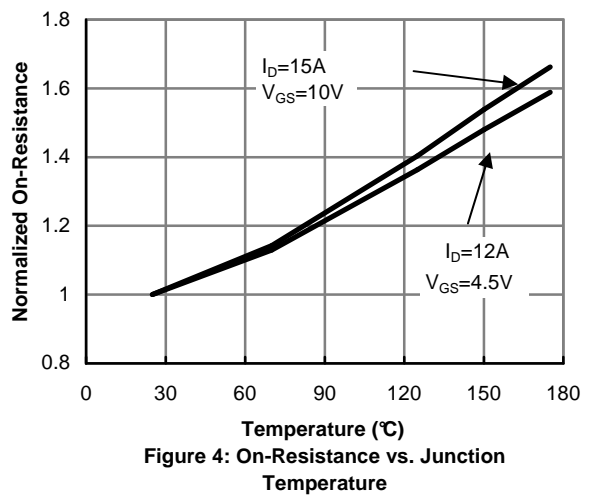


Figure 4: On-Resistance vs. Junction Temperature

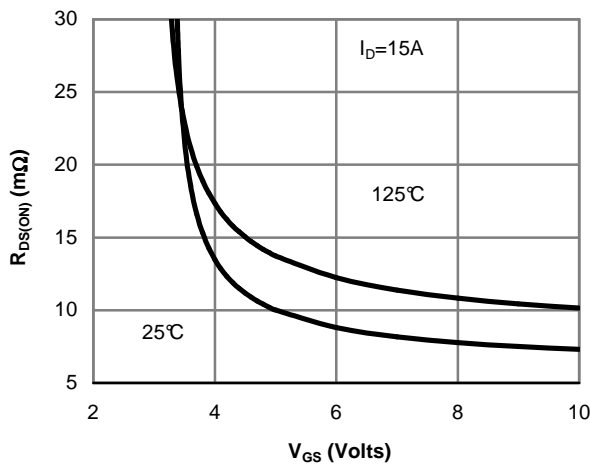


Figure 5: On-Resistance vs. Gate-Source Voltage

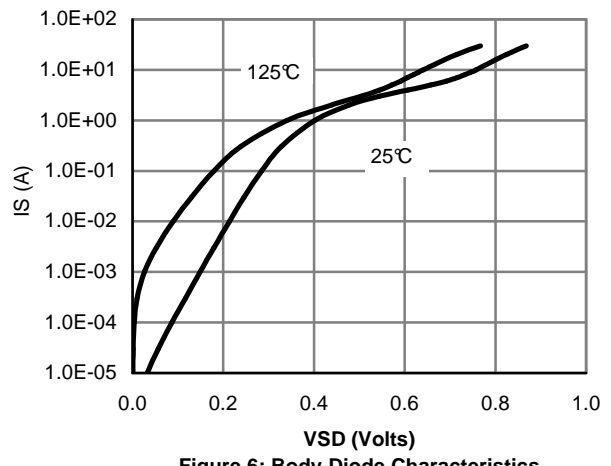


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

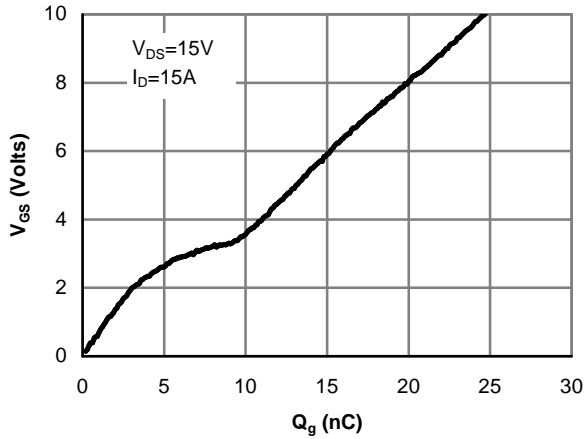


Figure 7: Gate-Charge Characteristics

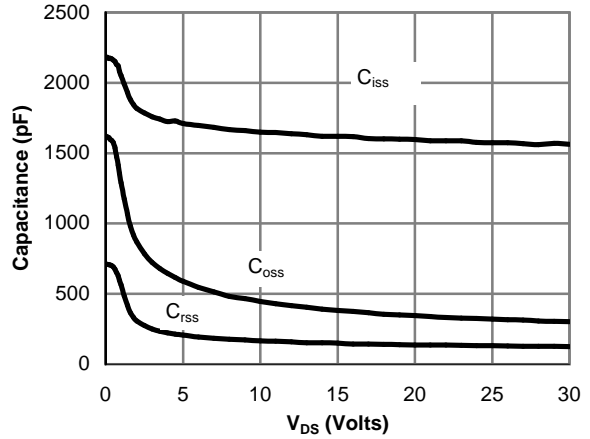


Figure 8: Capacitance Characteristics

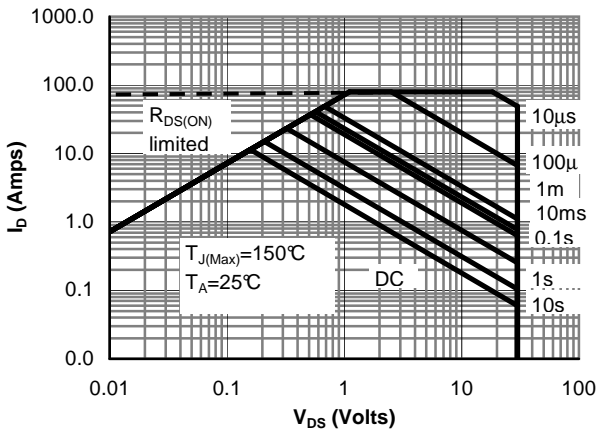


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

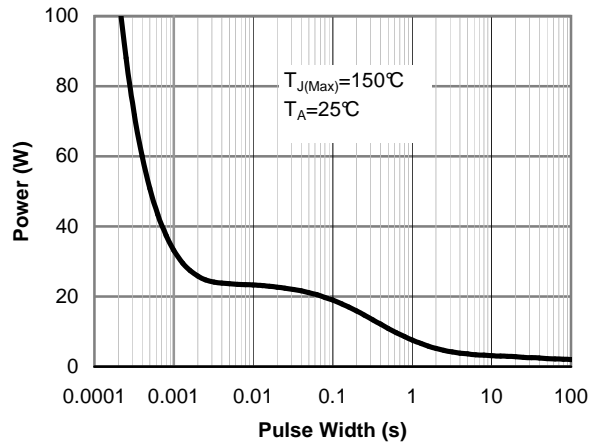


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

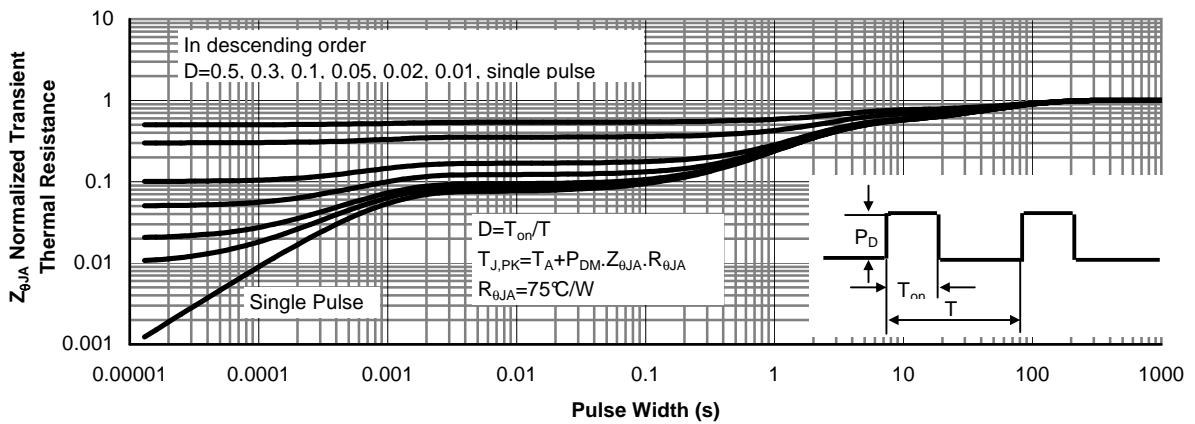
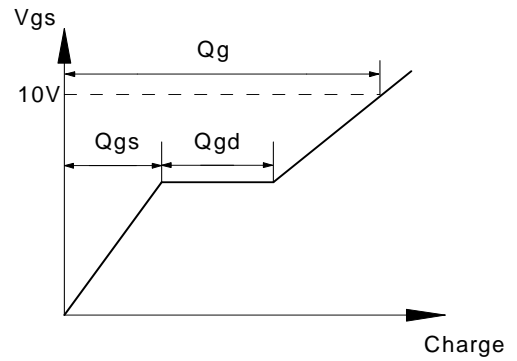
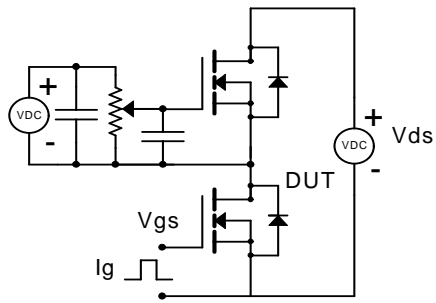
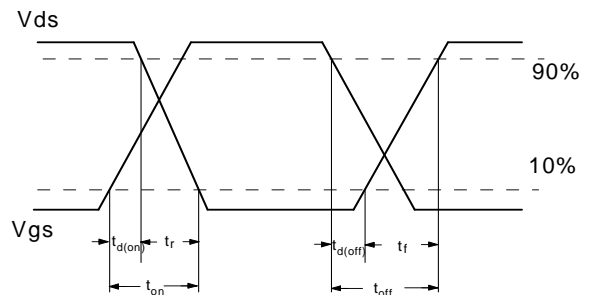
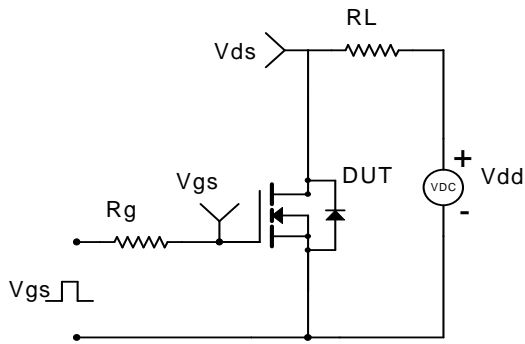


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

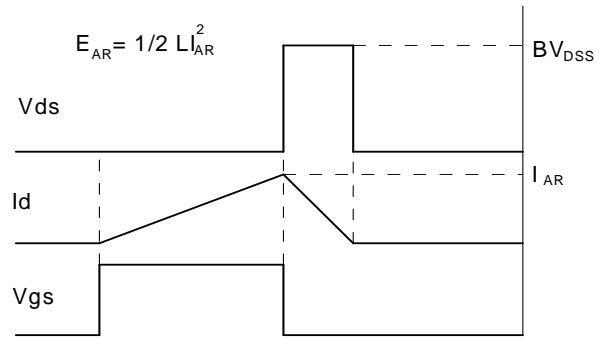
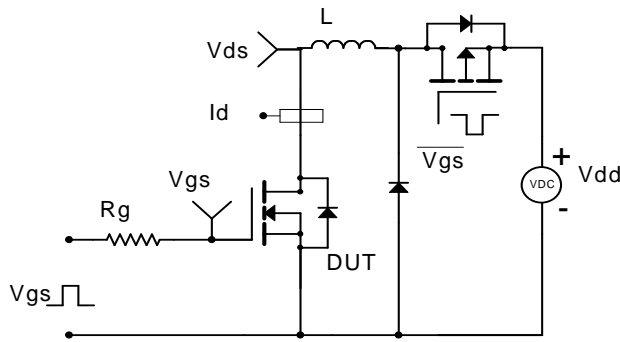
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

